

FORM PTO-1449 (Modified) INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Docket No. P0147US2-7	Application Number 10/665,595
	Applicant THIBEAULT, BRIAN et al.	
	Filing Date September 17, 2003	Group Art Unit

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number							Date	Name	Class	Subclass	Filing Date If Appropriate
J. T.	5	7	7	9	9	2	4	07/1998	KRAMES et al.	216	24	
	3	9	5	4	5	3	4	05/1976	SCIPRES et al.	156	7	
	5	7	9	3	0	6	2	08/1998	KISH et al.	257	98	
	5	3	5	9	2	0	8	10/1994	KATSUKI et al.	257	82	
	5	4	1	4	2	8	1	05/1995	WATABE et al.	257	95	
	5	4	9	1	3	5	0	02/1996	UNNO et al.	257	99	
	5	5	2	8	0	5	7	06/1996	YANAGASE et al.	257	96	
	5	5	5	7	1	1	5	09/1996	SHAKUDA	257	81	
	6	4	1	0	9	4	2	06/2002	THIBEAULT et al.	257	88	
	6	0	9	1	0	8	5	07/2000	LESTER	257	98	
J. T.	5	7	4	4	8	2	8	04/1998	NOZAKI et al.	257	94	

FOREIGN PATENT DOCUMENTS

	Document Number							Date	Country	Class	Subclass	Translation	
												Yes	No
J. T.	W0	99	5	3	5	7	8	10-21-99	PCT			X	
J. T.	11	2	7	4	5	6	8	10-08-99	JAPANESE				X
J. T.	W0	01	41	22	5	A	2	06-07-01	PCT			X	
J. T.	EP	09	77	27	7	A	1	11-13-98	EUROPE			X	
J. T.	DE	26	33	19	1	A	1	07-23-76	GERMAN				X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

1	Egawa et al. "STIMULATED EMISSION CURRENT INJECTED InGaN/AlGaN SURFACE EMITTING DIODE WITH Al REFLECTOR AT ROOM TEMPERATURE", pp. 486-488, Electronics Letters, 2/29/96, Vol 32, No. 5.
2	I. Schnitzer et al. "30% EXTERNAL QUANTUM EFFICIENCY FROM SURFACE TEXTURED, THIN-FILM LIGHT-EMITTING DIODES", 1993 American Institute of Physics, pp. 2174-2176.
Examiner	Date Considered
J. T.	7/22/04
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Date Considered

	1	A. KOCK AND E. GORNICK, <u>STRONGLY DIRECTIONAL EMISSION FROM AlGaAs/GaAs LIGHT-EMITTING DIODES</u> , Applied Physics Letters 57, pp. 2327-2329 (1990)
	2	KRAMS et al., <u>HIGH POWER TRUNCATED INVERTED PYRAMID (Al_{0.3}Ga_{0.7})_{0.5}In_{0.5}P/GaP LIGHT-EMITTING DIODES EXHIBITING >50% EXTERNAL QUANTUM EFFICIENCY</u> , Applied Physics Letters 75, pp. 2365-2367 (1999)
	3	SCHNITZER et al., <u>ULTRAHIGH SPONTANEOUS EMISSION QUANTUM EFFICIENCY, 99.7% INTERNALLY AND 72% EXTERNALLY, FROM AlGaAs/GaAs/AlGaAs DOUBLE HETEROSTRUCTURES</u> , Applied Physics Letters 62, pp. 131-133 (1993)
Examiner		
Date Considered	7/22/04	
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		